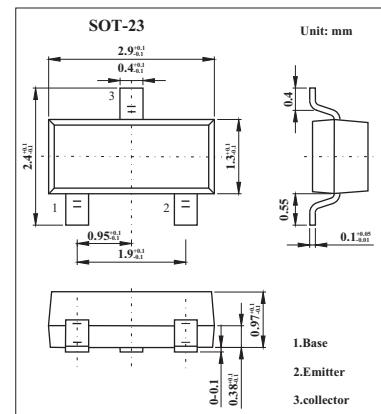


FMMT625

■ Features

- Collector current: $I_C = 1A$
- Power dissipation : $P_C = 625mW$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	150	V
Collector-emitter voltage	V_{CEO}	150	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	1	A
Base current	I_B	0.5	A
Power dissipation	P_C	625	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	°C

FMMT625

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	Ic=100 µ A	150			V
Collector-emitter breakdown voltage *	V(BR)CEO	Ic=10mA	150			V
Emitter-base breakdown voltage	V(BR)EBO	Ie=100 µ A	5			V
Collector cutoff current	IcBO	Vcb=130V			100	nA
Emitter cut-off current	IeBO	Veb=4V			100	nA
Collector emitter cutoff current	Ices	Vces=130V			100	nA
Collector-emitter saturation voltage *	Vce(sat)	Ic=0.1A, Ib=10mA		26	50	mV
		Ic=0.1A, Ib=1mA		110	200	mV
		Ic=1A, Ib=50mA		180	300	mV
Base-Emitter Saturation Voltage *	Vbe(sat)	Ic=1A, Ib=50mA*		0.85	1.0	V
Base-Emitter Turn-On Voltage *	Vbe(on)	Ic=1A, Vce=10V*		0.74	1.0	V
DC current gain	hFE	Ic=10mA, Vce=10V*	200	400		
		Ic=200mA, Vce=10V	300	450		
		Ic=1A, Vce=10V*	30	45		
		Ic=3A, Vce=10V*		15		
Output capacitance	Cob	Vcb=10V, f=1MHz		6	10	pF
Transition frequency	fr	Ic=50mA, Vce=10V, f=100MHz	100	135		MHz

* Pulse test: tp ≤ 300 µs; d ≤ 0.02.

■ Marking

Marking	625
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